ALPHA & OMEGA SEMICONDUCTOR, LTD.

Rev 2: Aug 2004

AO7403, AO7403L (Green Product)
P-Channel Enhancement Mode Field Effect Transistor

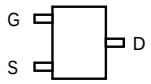
General Description

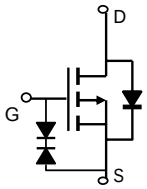
The AO7403 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge, and operation with gate voltages as low as 1.8V, in the small SOT323 footprint. It can be used for a wide variety of applications, including load switching, low current inverters and low current DC-DC converters. It is ESD protected to 2KV HBM. AO7403L (Green Poduct) is offered in a lead-free package.

Features

V_{DS} (V) = -20V
I_D = -0.7A
$R_{DS(ON)}$ < 470mΩ (V_{GS} = -4.5V)
$R_{DS(ON)}$ < 625mΩ (V_{GS} = -2.5V)
$R_{DS(ON)}$ < 900mΩ (V_{GS} = -1.8V)

SC-70
(SOT-323)
Top View





Absolute Maximum Ratings T_A=25°C unless otherwise noted

Parameter		Symbol	Maximum	Units
Drain-Source Voltage		V_{DS}	-20	V
Gate-Source Voltage		V_{GS}	±8	V
Continuous Drain Current [A]	T_A=25°C	I_D	-0.7	A
	T_A=70°C		-0.5	
Pulsed Drain Current [B]		I_{DM}	-3	
Power Dissipation [A]	T_A=25°C	P_D	0.35	W
	T_A=70°C		0.22	
Junction and Storage Temperature Range		T_J, T_{STG}	-55 to 150	°C

Thermal Characteristics

Parameter		Symbol	Typ	Max	Units
Maximum Junction-to-Ambient [A]	t ≤ 10s	$R_{\theta JA}$	300	360	°C/W
Maximum Junction-to-Ambient [A]	Steady-State		350	425	°C/W
Maximum Junction-to-Lead [C]	Steady-State	$R_{\theta JL}$	280	320	°C/W

Electrical Characteristics (T_J=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
STATIC PARAMETERS						
BV_{DSS}	Drain-Source Breakdown Voltage	I_D=-250µA, V_{GS}=0V	-20			V
I_{DSS}	Zero Gate Voltage Drain Current	V_{DS}=-16V, V_{GS}=0V			-1	µA
		T_J=55°C			-5	
I_{GSS}	Gate-Body leakage current	V_{DS}=0V, V_{GS}=±8V			±10	µA
$V_{GS(th)}$	Gate Threshold Voltage	V_{DS}=V_{GS} I_D=-250µA	-0.5	-0.6	-0.9	V
$I_{D(ON)}$	On state drain current	V_{GS}=-4.5V, V_{DS}=-5V	-3			A
$R_{DS(ON)}$	Static Drain-Source On-Resistance	V_{GS}=-4.5V, I_D=-0.7A		388	470	mΩ
		T_J=125°C		542	660	
		V_{GS}=-2.5V, I_D=-0.6A		519	625	mΩ
		V_{GS}=-1.8V, I_D=-0.5A		666	900	mΩ
g_{FS}	Forward Transconductance	V_{DS}=-5V, I_D=-0.7A		1.7		S
V_{SD}	Diode Forward Voltage	I_S=-0.5A,V_{GS}=0V		-0.86	-1	V
I_S	Maximum Body-Diode Continuous Current				-0.4	A
DYNAMIC PARAMETERS						
C_{iss}	Input Capacitance	V_{GS}=0V, V_{DS}=-10V, f=1MHz		114		pF
C_{oss}	Output Capacitance			17		pF
C_{rss}	Reverse Transfer Capacitance			14		pF
R_g	Gate resistance	V_{GS}=0V, V_{DS}=0V, f=1MHz		12		Ω
SWITCHING PARAMETERS						
Q_g	Total Gate Charge	V_{GS}=-4.5V, V_{DS}=-10V, I_D=-0.7A		1.44		nC
Q_{gs}	Gate Source Charge			0.14		nC
Q_{gd}	Gate Drain Charge			0.35		nC
$t_{D(on)}$	Turn-On DelayTime	V_{GS}=-4.5V, V_{DS}=-10V, R_L=14.3Ω, R_{GEN}=3Ω		6.5		ns
t_r	Turn-On Rise Time			6.5		ns
$t_{D(off)}$	Turn-Off DelayTime			18.2		ns
t_f	Turn-Off Fall Time			5.5		ns
t_{rr}	Body Diode Reverse Recovery Time	I_F=-0.7A, dI/dt=100A/µs		10		ns
Q_{rr}	Body Diode Reverse Recovery Charge	I_F=-0.7A, dI/dt=100A/µs		3		nC

A: The value of $R_{\theta JA}$ is measured with the device mounted on 1in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A =25°C. The value in any a given application depends on the user's specific board design. The current rating is based on the t≤ 10s thermal resistance rating.

B: Repetitive rating, pulse width limited by junction temperature.

C. The $R_{\theta JA}$ is the sum of the thermal impedence from junction to lead $R_{\theta JL}$ and lead to ambient.

D. The static characteristics in Figures 1 to 6,12,14 are obtained using 80µs pulses, duty cycle 0.5% max.

E. These tests are performed with the device mounted on 1 in^2 FR-4 board with 2oz. Copper, in a still air environment with T_A=25°C. The SOA curve provides a single pulse rating.

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TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

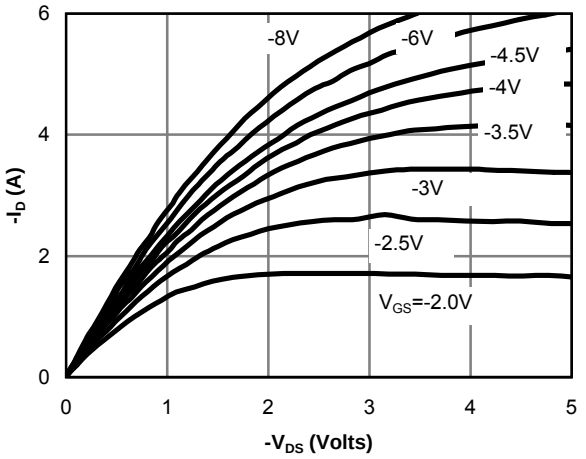


Fig 1: On-Region Characteristics

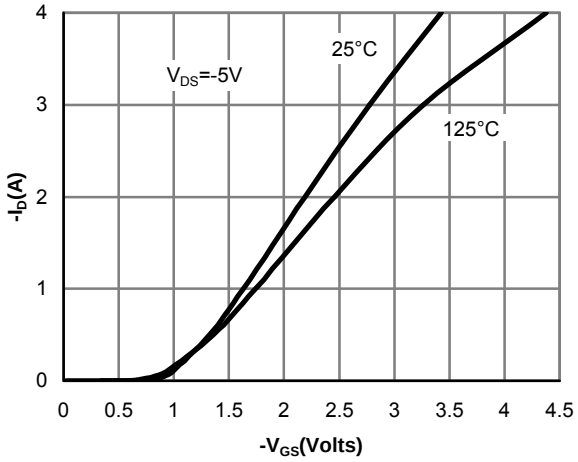


Figure 2: Transfer Characteristics

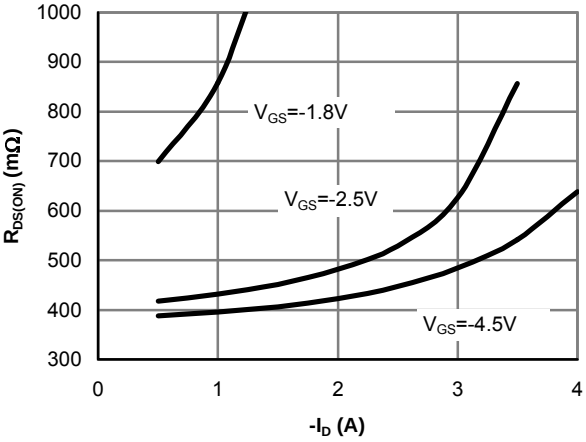


Figure 3: On-Resistance vs. Drain Current and Gate Voltage

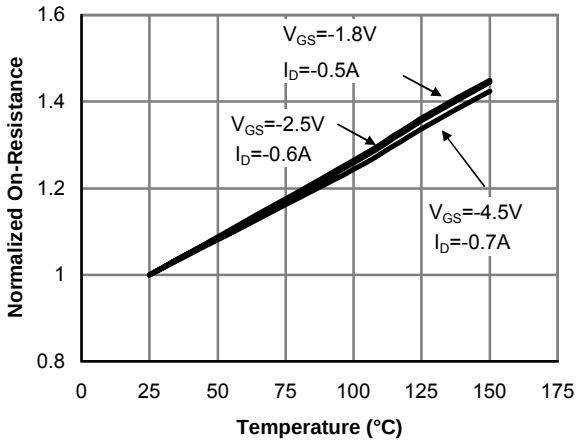


Figure 4: On-Resistance vs. Junction Temperature

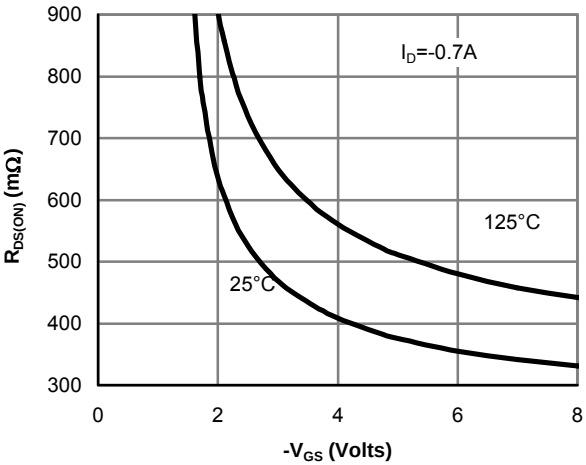


Figure 5: On-Resistance vs. Gate-Source Voltage

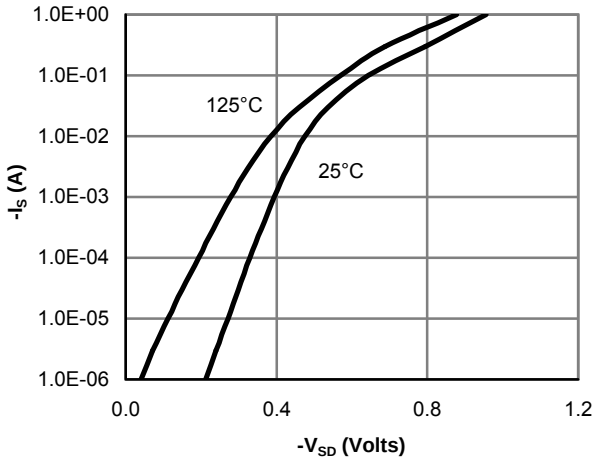


Figure 6: Body-Diode Characteristics

TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

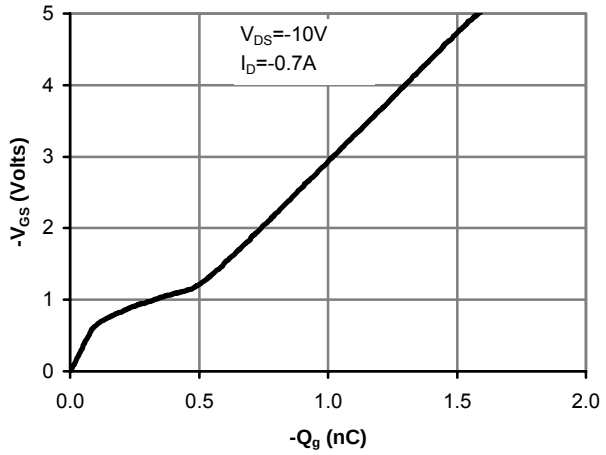


Figure 7: Gate-Charge Characteristics

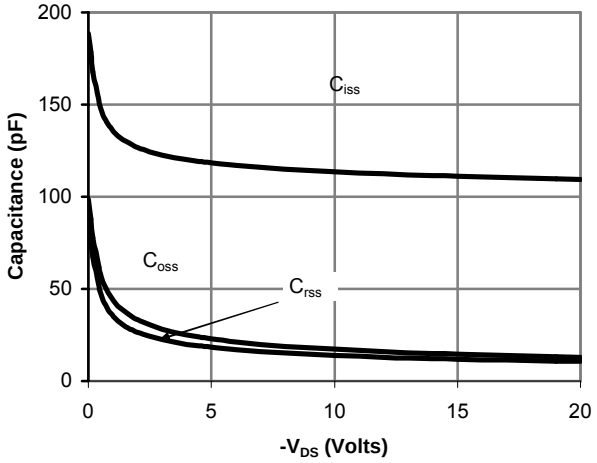


Figure 8: Capacitance Characteristics

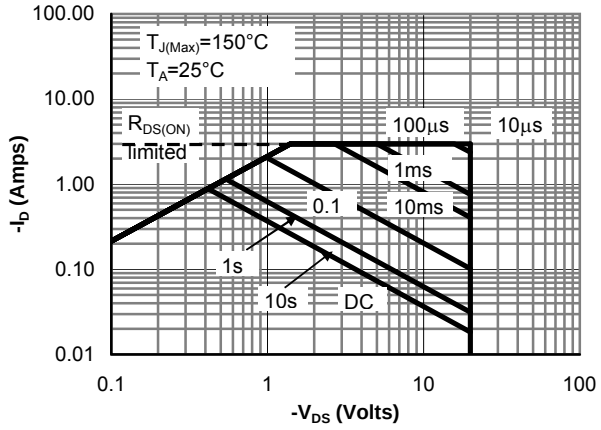


Figure 9: Maximum Forward Biased Safe Operating Area (Note E)

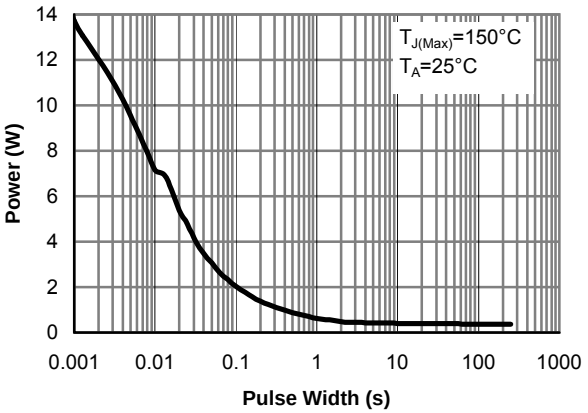


Figure 10: Single Pulse Power Rating Junction-to-Ambient (Note E)

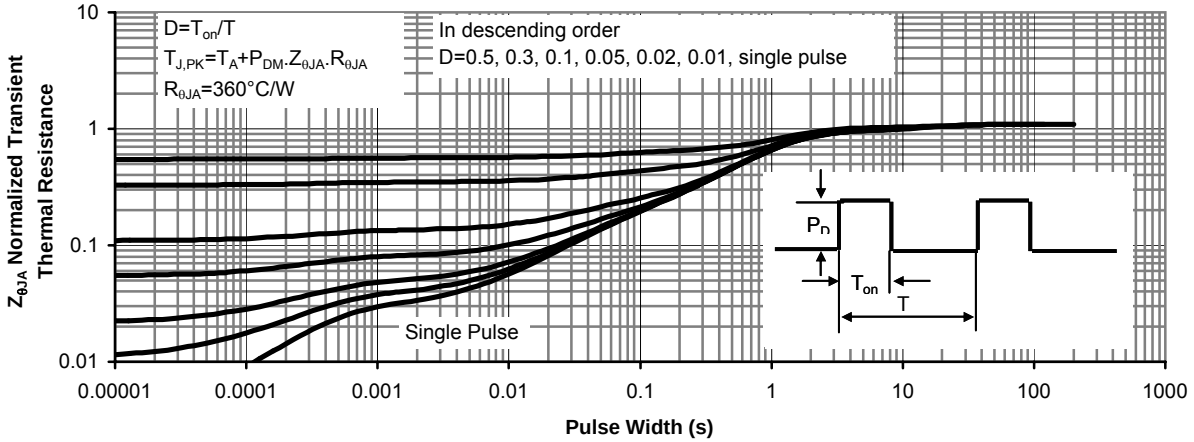
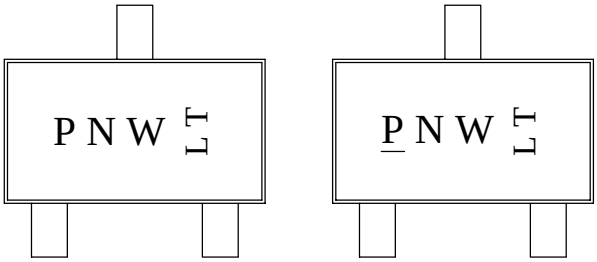


Figure 11: Normalized Maximum Transient Thermal Impedance

Document No.	PD-00128
Version	rev C
Title	AO7403 Marking Description

ALPHA & OMEGA SEMICONDUCTOR, LTD.

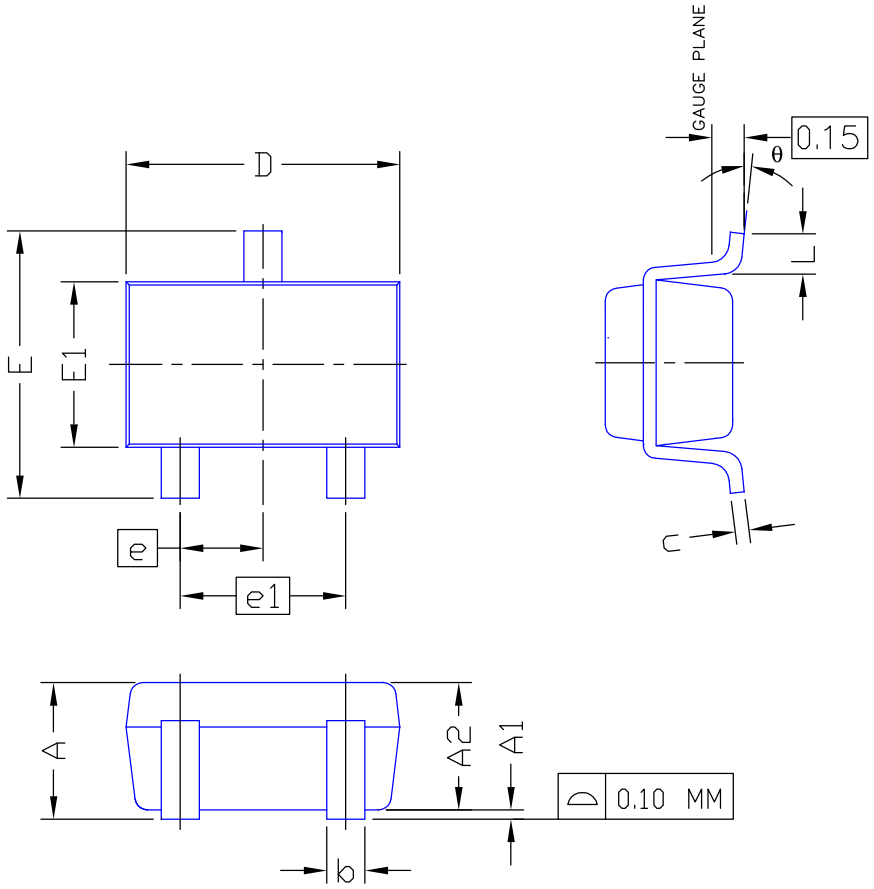
SC-70(3L) PACKAGE MARKING DESCRIPTION



Standard product Green product

NOTE:
P - Product number code
N - Assembly&Foundry location code
W - Year and Week code
LT - Assembly lot code.

PART NO.	DESCRIPTION	CODE (P&N)
AO7403	Standard product	3&N
AO7403L	Green product	$\underline{3}$&N

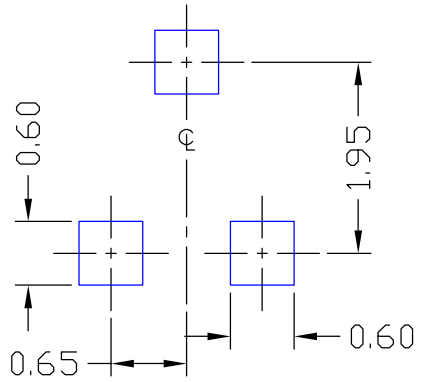


NOTE

1.ALL DIMENSIONS ARE IN MILLMETERS.
2.DIMENSIONS ARE INCLUSIVE OF PLATING.
3.PACKAGE BODY SIZES EXCLUDE MOLD FLASH AND GATE BURRS.
4.DIE IS FACING UP FOR MOLD AND FACING DOWN FOR TRIM/FORM .ie:REVERSE TRIM/FORM.
5. DIMENSION L IS MEASURED IN GAUGE PLANE.
6. CONTROLLING DIMENSION IS MILLIMETER. CONVERTED INCH DIMENSIONS ARE NOT NECESSARILY EXACT.

SYMBOLS	DIMENSIONS IN MILLIMETERS			DIMENSIONS IN INCHES		
	MIN	NOM	MAX	MIN	NOM	MAX
A		---	1.10		---	0.043
A1	0.00	---	0.10	0.00	---	0.004
A2	0.7	0.9	1.00	0.028	0.035	0.039
b	0.15	---	0.30	0.006	---	0.012
c	0.08	---	0.22	0.003	---	0.009
D	1.85	2.10	2.15	0.073	0.083	0.085
E	1.80	2.30	2.40	0.071	0.091	0.094
e	0.65 BSC			0.026 BSC		
e1	1.30 BSC			0.051 BSC		
E1	1.1	1.30	1.4	0.043	0.051	0.055
L	0.26	0.36	0.46	0.010	0.014	0.018
θ	0°	4°	8°	0°	4°	8°

RECOMMENDATION OF LAND PATTERN



UNIT: mm

UNLESS OTHERWISE SPECIFIED DIMENSIONS ARE IN INCHES

DECIMAL ANGULAR
X.X ± ±
X.XX ±
X.XXX ±

INTERPRET DIM AND TOL PER ASME Y14.5M – 1994

PRINTING IS SCALED TO FIT DO NOT SCALE DRAWING

THIRD ANGLE PROJECTION

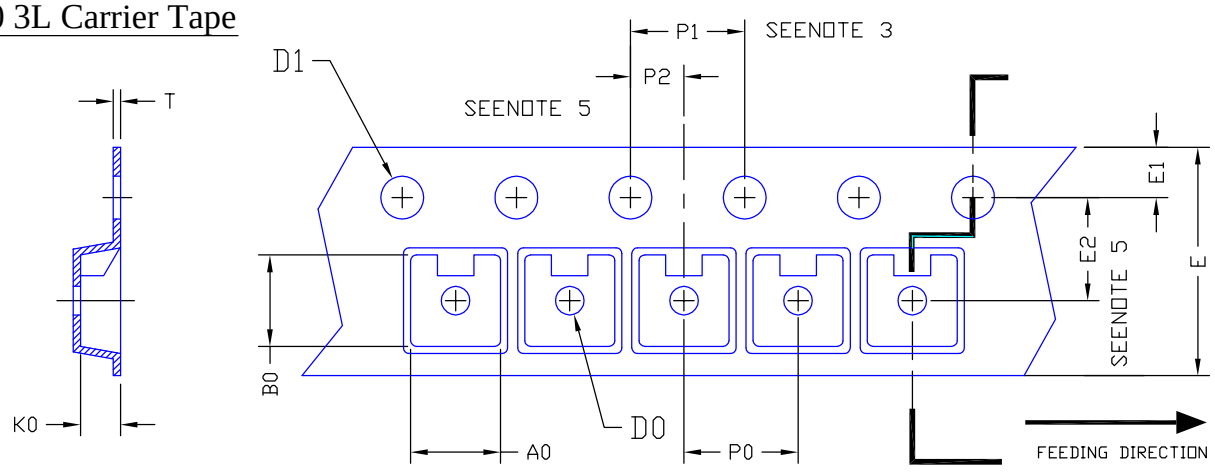
ALPHA & OMEGA SEMICONDUCTOR, LTD.

Document No.	PD-00012
Version	rev C
Title	SC-70-3L PACKAGE OUTLINE

ALPHA & OMEGA
SEMICONDUCTOR, LTD.

SC-70 3L Tape and Reel Data

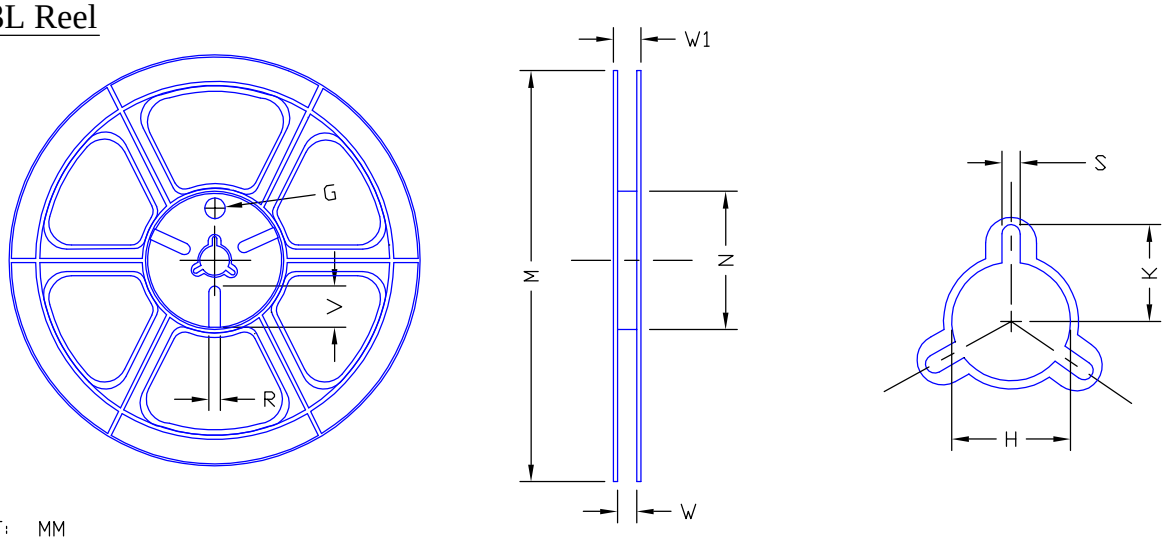
SC-70 3L Carrier Tape



UNIT: MM

PACKAGE	A0	B0	K0	D0	D1	E	E1	E2	P0	P1	P2	T
SOT-23 (8 mm)	2.40 ±0.10	2.40 ±0.10	1.19 ±0.10	1.00 MIN	1.55 ±0.05	8.00 ±0.30	1.75 ±0.10	3.50 ±0.05	4.00 ±0.10	4.00 ±0.10	2.00 ±0.05	0.25 ±0.05

SC-70 3L Reel



UNIT: MM

TAPE SIZE	REEL SIZE	M	N	W	W1	H	K	S	G	R	V
8 mm	ø180	ø180.00 ±0.50	ø60.50	9.00 ±0.30	11.40 ±1.00	ø13.00 +0.50 −0.20	10.60	2.00 ±0.50	ø9.00	5.00	18.00

SC-70 3L Tape

Leader / Trailer & Orientation